L	Hit:	S Search Text	DB	Time stame
Number 7			DB .	Time stamp
1'	910	O (aln or aluminum adj nitride) same (MBE or mocvd or hydride adj vapor or hvpe or	USPAT;	2004/06/10
1	1	molecular near2 beam or metal near2	US-PGPUB; EPO; JPO;	13:51
i		organic)	DERWENT;	
8	30	1 (-33 )	IBM_TDB	
"	30	) (aln or aluminum adj nitride) same (MBE or molecular near2 beam) near10 (mocvd or	USPAT;	2004/06/10
1		metal near2 organic) near10 (hydride	US-PGPUB; EPO; JPO;	15:15
		near2 vapor or hvpe)	DERWENT;	
9			IBM TDB	
	25	(aln or aluminum adj nitride) near10 (MBE or molecular near2 beam) near10 (mocvd or	USPAT;	2004/06/10
		metal near2 organic)	US-PGPUB; EPO; JPO;	13:53
		-	DERWENT;	
10	226	/-3	IBM_TDB	
110	226	(aln or aluminum adj nitride) near10	USPAT;	2004/06/10
		junction	US-PGPUB; EPO; JPO;	15:15
1			DERWENT;	
11	21	(-11	IBM_TDB	
	21	(aln or aluminum adj nitride) near10 junction near3 pn	USPAT;	2004/06/10
		Janotion hears ph	US-PGPUB; EPO; JPO;	15:23
1			DERWENT;	
12	5	14-44	IBM_TDB	
12	*	(indium adj nitride or inn) near10 junction near3 pn	USPAT;	2004/06/10
	1	Janetion hears pit	US-PGPUB; EPO; JPO;	15:49
1			DERWENT;	
13	1 111	/	IBM_TDB	
1 13	111		USPAT;	2004/06/10
		(gan or gallium adj nitride or "iii-v")	US-PGPUB; EPO; JPO;	15:50
			DERWENT;	
14	2	1	IBM_TDB	
17	-	(zno or zinc adj oxide) near5 buffer near10 amorphous same (gan or gallium adj	USPAT;	2004/06/10
		nitride or "iii-v")	US-PGPUB; EPO; JPO;	15:51
	1		DERWENT;	
15	,	H11242000	IBM TDB	
15	2	"11243229"	USPĀT;	2004/06/10
	1		US-PGPUB; EPO; JPO;	15:58
l			DERWENT;	
16	45	(and an aire and an aire	IBM_TDB	1
1 - 0	4.3	(zno or zinc adj oxide) near10 (polycrystal\$5) same varistor	USPAT;	2004/06/10
		Transfer variation	US-PGPUB; EPO; JPO;	16:21
			DERWENT;	
17	3	/Zno or ging add anddah access a sa	IBM_TDB	
	1	(zno or zinc adj oxide) near5 buffer same pn near2 junction	USPAT; US-PGPUB;	2004/06/10
		<del>-                                    </del>	EPO; JPO;	16:22
			DERWENT;	
18	985	iunction near10 (gan on gallium :	IBM_TDB	
,	-53	junction near10 (gan or gallium adj nitride or "iii-v")	USPAT; US-PGPUB;	2004/06/10
	; I	·= · ,	EPO; JPO;	16:23
			DERWENT;	
19	29	(junction near10 (gar11)	IBM_TDB	
	J	(junction near10 (gan or gallium adj nitride or "iii-v")) same (zno or zinc	USPAT; US-PGPUB;	2004/06/10
	2	adj oxide)	EPO; JPO;	16:26
	, i.s.	,	DERWENT;	
20	3	"04068579"	IBM_TDB	
		04000373	USPĀT; US-PGPUB;	2004/06/10
			EPO; JPO;	16:59
			DERWENT;	
			IBM TDB	

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21		I tetsuzo none undo in and anim need	T.100	T *** * *** * ***
	-	tetsuzo near2 ueda.in. and spin near2	USPAT; US-PGPUB;	2004/06/10
			EPO; JPO;	16:59
			DERWENT;	
			IBM TDB	
-	34		USPAT;	2003/09/22
i		adj treat\$4 or crystalliz\$4 or rta or	US-PGPUB;	11:02
		rtp) and 117/\$4.ccls.	EPO; JPO;	
1	1		DERWENT;	
-	0	(III-V or nitride) near5 solution same	IBM_TDB	10000 /00 /00
1		anneal\$4 same crystalliz\$4 and	USPAT; US-PGPUB;	2003/09/22
		117/\$4.ccls.	EPO; JPO;	11:04
1	1		DERWENT;	
			IBM TDB	1
-	2		USPAT;	2003/09/22
	l l	crystalliz\$4 and 117/\$4.ccls.	US-PGPUB;	11:05
			EPO; JPO;	
			DERWENT;	
-	15	(III-V or nitride) near5 solution same	IBM_TDB	
İ	1	film and 117/\$4.ccls.	USPAT; US-PGPUB;	2003/09/22
		1	EPO; JPO;	11:11
	1		DERWENT;	
			IBM TDB	
1-	209		USPĀT;	2003/09/22
		crystalliz\$4) same film and 117/\$4.ccls.	US-PGPUB;	11:25
			EPO; JPO;	
			DERWENT;	
-	4	solution near10 (crystal\$4 or	IBM_TDB USPAT;	2003/09/22
1		crystalliz\$4) same film same "III-V" and	US-PGPUB;	11:28
		117/\$4.ccls.	EPO; JPO;	111.20
	,		DERWENT;	
_	1.2		IBM_TDB	1
-	13		USPAT;	2003/09/22
	1	crystalliz\$4) same film same "nitride" and 117/\$4.ccls.	US-PGPUB;	11:30
		and 11// 94.0013.	EPO; JPO;	
1	1		DERWENT; IBM_TDB	
-	2	nitride near10 solution same (anneal\$ or	USPAT;	2003/09/22
İ		rapid adj thermal or heat adj treat\$4 or	US-PGPUB;	11:31
		rta or rtp or ptp) and 117/\$4.ccls.	EPO; JPO;	
			DERWENT;	
l _	667	nitrido populoluti	IBM_TDB	
	00/	nitride near10 solution same (anneal\$ or rapid adj thermal or heat adj treat\$4 or	USPAT;	2003/09/22
		rta or rtp or ptp)	US-PGPUB;	11:32
		Debi	EPO; JPO; DERWENT;	
			IBM TDB	
-	0	nitride near10 solution same (anneal\$ or	USPAT;	2003/09/22
		rapid adj thermal or heat adj treat\$4 or	US-PGPUB;	11:32
	1 1	rta or rtp or ptp) same (crystal\$4 or	EPO; JPO;	
		crystalliz\$4) same spin	DERWENT;	
_	l an	nitride near10 solution same (anneal\$ or	IBM_TDB	
	1 301	rapid adj thermal or heat adj treat\$4 or	USPAT;	2003/09/22
		rta or rtp or ptp) same (crystal\$4 or	US-PGPUB; EPO; JPO;	11:32
	]	crystalliz\$4)	DERWENT;	
			IBM TDB	1
-	0	nitride near10 solution same (anneal\$ or	USPAT;	2003/09/22
	1	rapid adj thermal or heat adj treat\$4 or	US-PGPUB;	11:32
		rta or rtp or ptp) same (crystal\$4 or	EPO; JPO;	
	1	crystalliz\$4) same "iii-v"	DERWENT;	
_	3	"iii-v" near10 solution same (anneal\$ or	IBM_TDB	2222/22/22
		rapid adj thermal or heat adj treat\$4 or	USPAT; US-PGPUB;	2003/09/22
	j	rta or rtp or ptp) same (crystal\$4 or	EPO; JPO;	11:55
	l·	crystalliz\$4)	DERWENT;	
	<u> </u>		IBM TDB	

		<u></u>	,	
-	444946	anneal\$ or rapid adj thermal or heat adj treat\$4 or rta or rtp or ptp	USPAT; US-PGPUB;	2003/09/22
		i creator of fita of fitp of pep	EPO; JPO;	11.55
İ			DERWENT;	
1_	37679	spin mand mands	IBM_TDB USPAT;	2003/09/22
-	3/6/9	spin near4 coat\$4	US-PGPUB;	11:56
1			EPO; JPO;	11.00
			DERWENT;	
	,	4	IBM_TDB	2002/20/20
-	3	((spin near4 coat\$4) same ("IIi-v" or "III" near4 nitride)) same (anneal\$ or	USPAT; US-PGPUB;	2003/09/22 11:56
	. 1	rapid adj thermal or heat adj treat\$4 or	EPO; JPO;	11.36
1	6 1	rta or rtp or ptp)	DERWENT;	
1	1		IBM_TDB	
-	46	(spin near4 coat\$4) same ("IIi-v" or "III" near4 nitride)	USPAT; US-PGPUB;	2003/09/22 13:24
	1 %	III heard hittige/	EPO; JPO;	13:24
			DERWENT;	
			IBM_TDB	
-	4	heat\$4 near10 ligand same "III-v"	USPAT;	2003/09/22
	1		US-PGPUB; EPO; JPO;	13:26
'			DERWENT;	1
	, ·		IBM_TDB	
-	0	solution near10 ligand same "III-v"	USPAT;	2003/09/22
1			US-PGPUB;	13:26
1			EPO; JPO; DERWENT;	
1			IBM_TDB	
-	1	solution near10 heat\$4 near10 (volatile	USPAT;	2003/09/22
		or vaporiz\$4) same "III-v"	US-PGPUB;	13:27
			EPO; JPO; DERWENT;	
			IBM TDB	
-	65	solution near10 heat\$4 near10 (volatile	USPĀT;	2003/09/22
		or vaporiz\$4) and spin near4 coat\$4	US-PGPUB;	13:28
			EPO; JPO;	
			DERWENT; IBM TDB	
-	6	solution near10 heat\$4 near10 (volatile	USPAT;	2003/09/22
		or vaporiz\$4) same spin near4 coat\$4	US-PGPUB;	13:29
			EPO; JPO;	
			DERWENT; IBM TDB	
-	77	spin near4 coat\$4 same ("iii-v" or "iii"	USPAT;	2003/09/22
		near3 nitride or gan or gallium adj	US-PGPUB;	13:31
		nitride)	EPO; JPO;	
			DERWENT; IBM TDB	
-	42	spin near4 coat\$4 same ("iii-v" or "iii"	USPAT;	2003/09/22
		near3 nitride or gan or gallium adj	US-PGPUB;	13:44
		nitride) not same (photoresist or resist)	EPO; JPO;	
			DERWENT; IBM TDB	
-	6	("5433169"   "5923950"   "5989338"	USPAT	2003/09/22
		"5997639"   "6146457"   "6176925").PN.		13:35
-	96	("iii-v" or "iii" near3 nitride or gan or	USPAT;	2003/09/22
		gallium adj nitride) same (crystal\$4 or	US-PGPUB;	13:45
		crystalliz\$4 or crystalline) same precursor	EPO; JPO; DERWENT;	1
]		•	IBM TDB	
-	38	("iii-v" or "iii" near3 nitride or gan or	USPĀT;	2003/09/22
		gallium adj nitride) same (crystal\$4 or	US-PGPUB;	13:47
		crystalliz\$4 or crystalline) near10 precursor	EPO; JPO; DERWENT;	
	20		IBM TDB	
-	10	("iii-v" or "iii" near3 nitride or gan or	USPAT;	2003/09/22
		gallium adj nitride) same (crystal\$4 or	US-PGPUB;	13:47
		crystalliz\$4 or crystalline) near10 precursor same solution	EPO; JPO; DERWENT;	
1		breedragt same soldclon	IBM TDB	

				2004/06/01
_	87	spin near2 coat\$5 same ("iii-v" or gan or	USPAT;	2004/06/01
		gallium adj nitride)	US-PGPUB;	14:22
	i		EPO; JPO;	
			DERWENT;	
			IBM_TDB	2024/25/21
_	2090	(gan or gallium adj nitride) near4 buffer	USPAT;	2004/06/01
		near5 (layer or film)	US-PGPUB;	14:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	143	(gan or gallium adj nitride) near4 buffer	USPAT;	2004/06/01
	1	near5 (layer or film) same (aluminum adj	US-PGPUB;	14:22
		nitride)	EPO; JPO;	
		112 12 12 1	DERWENT;	
			IBM_TDB	
_	33	(gan or gallium adj nitride) adj buffer	USPAT;	2004/06/01
		near5 (layer or film) same (aluminum adj	US-PGPUB;	14:24
	1	nitride)	EPO; JPO;	
	1	micriac,	DERWENT;	
			IBM TDB	
	35	(gan or gallium adj nitride) adj buffer	USPAT;	2004/06/01
_	1 33	near5 (layer or film) same (inn indium	US-PGPUB;	14:30
		adj nitride)	EPO; JPO;	
	1	auj mittue/	DERWENT;	
	1		IBM TDB	
	16	(gan or gallium adj nitride) adj buffer	USPAT;	2004/06/01
-	16	near5 (layer or film) same (indium or	US-PGPUB;	14:41
		aluminum) near10 thick\$5	EPO; JPO;	
		aluminum) nearlo chick\$5	DERWENT;	
			IBM TDB	1
		H0000640H	USPAT;	2004/06/01
-	2	"0999640"	US-PGPUB;	14:35
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
			USPAT;	2004/06/01
-	5	"999640"		14:35
1		i '	US-PGPUB;	14.33
			EPO; JPO;	i
			DERWENT;	
			IBM_TDB	2004/06/01
-	0	(gan or gallium adj nitride) adj buffer	USPAT;	2004/06/01
1	1	near5 (layer or film) same (indium or	US-PGPUB;	14:45
l		aluminum) same pn	EPO; JPO;	
	1		DERWENT;	[ 1
			IBM_TDB	10004/06/03
l -	7		USPAT;	2004/06/01
1	1	near5 (layer or film) same pn	US-PGPUB;	15:21
1	1	1	EPO; JPO;	[
	1		DERWENT;	1
	1		IBM_TDB	1 / /
l _	27	(aluminum adj nitride or aln) near10 pn	USPAT;	2004/06/01
	1	<u> </u>	US-PGPUB;	15:24
	1		EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
l _	67	spin near2 coat\$5 same (aluminum adj	USPAT;	2004/06/01
	1	nitride)	US-PGPUB;	15:26
	ş		EPO; JPO;	1
			DERWENT;	
1	1		IBM TDB	
1	* 10	spin near2 coat\$5 near15 (aluminum adj	USPAT;	2004/06/01
1-	1	nitride)	US-PGPUB;	15:26
1	1	11102140/	EPO; JPO;	
1	1		DERWENT;	•
1	1		IBM TDB	
1	1			